



BSS138K

#### 50V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
50V	3.5Ω @ V <sub>GS</sub> = 10V	0.31A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switch

## **Features**

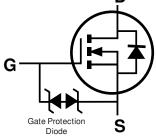
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/quality/product-definitions/

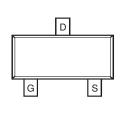
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)









Top View

Internal Schematic

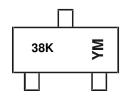
Top View

### Ordering Information (Note 4)

Part Number	Case	Packaging
BSS138K-7	SOT23	3,000/Tape & Reel
BSS138K-13	SOT23	10,000/Tape & Reel

- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



38K = Product Type Marking Code YM = Date Code Marking Y or \overline{Y}= Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	9	2020	2021	202	22	2023	2024	20	25	2026
Code	F	G		Н		J		K	L	N	Л	N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	q	0	N	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	50	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	ΙD	0.31 0.25	Α	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	I <sub>S</sub>	0.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I <sub>DM</sub>	0.8	A

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	0.38	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	338	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	0.54	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	237	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

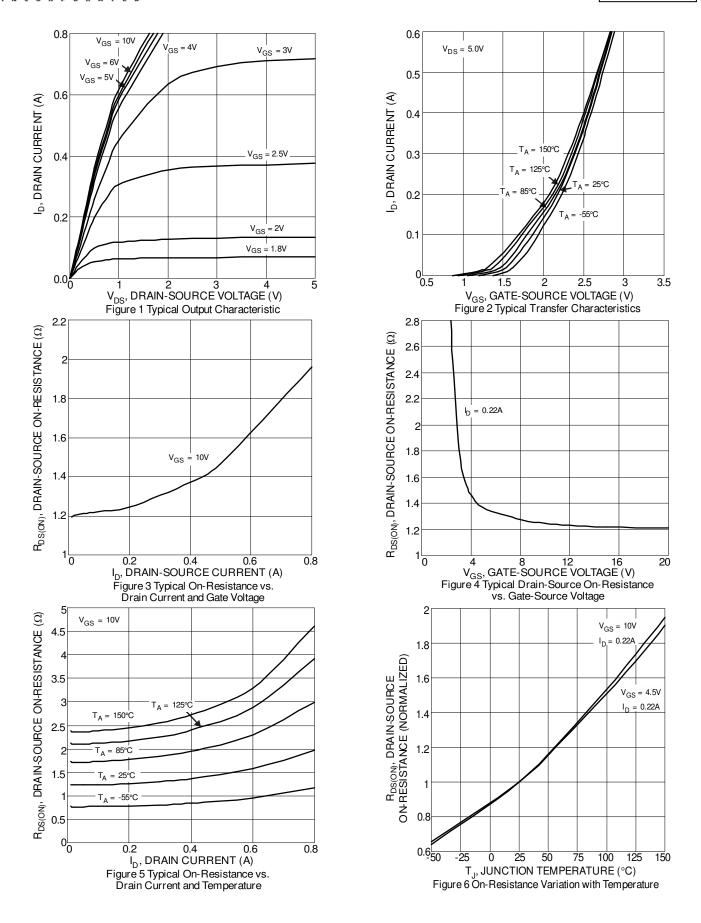
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 50V$ , $V_{GS} = 0V$		
Gate-Source Leakage	IGSS	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	1.1	1.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.3	3.5	Ω	$V_{GS} = 10V, I_D = 0.22A$		
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	V	$V_{GS} = 0V, I_D = 0.22A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	_	23.2	_	pF			
Output Capacitance	Coss	_	3.1	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ -f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	1	2.2	_	pF	1 - 1.00012		
Gate Resistance	$R_g$	-	69	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_g$	_	0.45	_	nC			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$		0.95	_	nC	$V_{DS} = 25V$ , $I_D = 0.2A$		
Gate-Source Charge	Qgs	-	0.10	_	nC	$\int_{0}^{\infty} V_{DS} = 25V, I_{D} = 0.2A$		
Gate-Drain Charge	$Q_{gd}$	_	0.14	_	nC			
Turn-On Delay Time	t <sub>D(ON)</sub>	1	3.2	_	ns			
Turn-On Rise Time	t <sub>R</sub>	_	2.5	_	ns	$V_{DS} = 25V, V_{GS} = 10V,$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	13.8	_	ns	$R_G = 50\Omega, I_D = 0.2A$		
Turn-Off Fall Time	t <sub>F</sub>	-	7.6	_	ns			
Reverse Recovery Time	t <sub>RR</sub>	-	8.8	_	ns	$I_F = 0.2A$ , $di/dt = 100A/\mu s$		
Reverse Recovery Charge	Q <sub>RR</sub>	_	2.6	_	nC	$I_F = 0.2A$ , $di/dt = 100A/\mu s$		

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

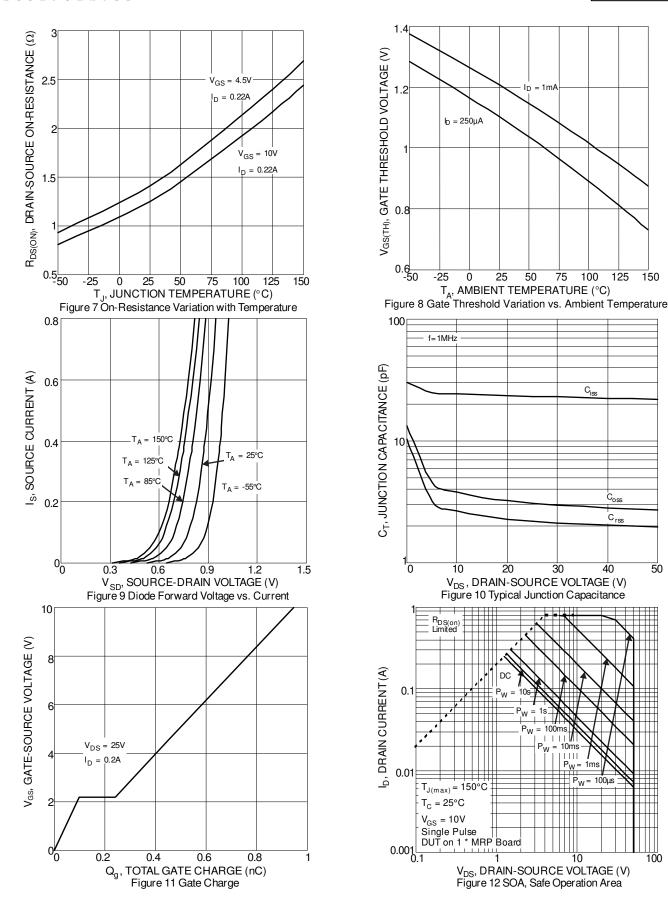
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided. 7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





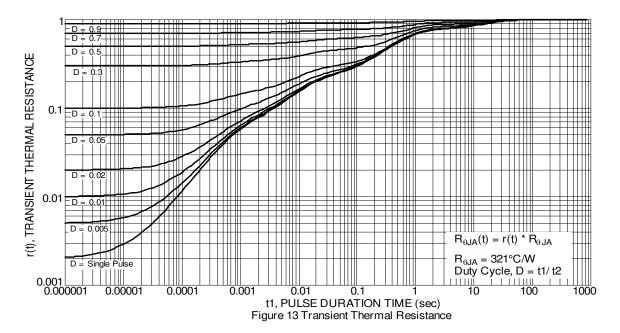




100

50



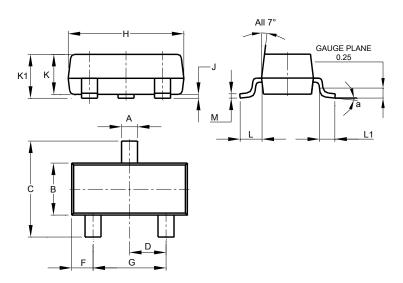




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

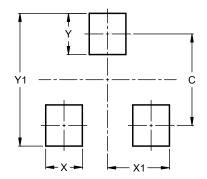


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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